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Applications of "<u>Embedded - Microcontrollers</u>"

Dataila	
Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100jggfa-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(11/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	Mounted	A	R5F100PFAFB#V0, R5F100PGAFB#V0, R5F100PHAFB#V0, R5F100PJAFB#V0, R5F100PKAFB#V0, R5F100PLAFB#V0 R5F100PFAFB#X0, R5F100PGAFB#X0, R5F100PHAFB#X0,
			D	R5F100PJAFB#X0, R5F100PKAFB#X0, R5F100PLAFB#X0 R5F100PFDFB#V0, R5F100PGDFB#V0, R5F100PHDFB#V0, R5F100PJDFB#V0, R5F100PKDFB#V0, R5F100PLDFB#V0
				R5F100PFDFB#X0, R5F100PGDFB#X0, R5F100PHDFB#X0, R5F100PJDFB#X0, R5F100PKDFB#X0, R5F100PLDFB#X0
			G	R5F100PFGFB#V0, R5F100PGGFB#V0, R5F100PHGFB#V0, R5F100PJGFB#V0 R5F100PFGFB#X0, R5F100PGGFB#X0, R5F100PHGFB#X0,
		Not mounted	A	R5F100PJGFB#X0  R5F101PFAFB#V0, R5F101PGAFB#V0, R5F101PHAFB#V0, R5F101PJAFB#V0, R5F101PKAFB#V0, R5F101PLAFB#V0
				R5F101PFAFB#X0, R5F101PGAFB#X0, R5F101PHAFB#X0, R5F101PJAFB#X0, R5F101PKAFB#X0, R5F101PLAFB#X0
			D	R5F101PFDFB#V0, R5F101PGDFB#V0, R5F101PHDFB#V0, R5F101PJDFB#V0, R5F101PKDFB#V0, R5F101PLDFB#V0 R5F101PFDFB#X0, R5F101PFDFB#X0, R5F101PHDFB#X0,
				R5F101PJDFB#X0, R5F101PKDFB#X0, R5F101PLDFB#X0
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	Mounted	A	R5F100PFAFA#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFA#V0, R5F100PKAFA#V0, R5F100PLAFA#V0 R5F100PFAFA#X0, R5F100PGAFA#X0, R5F100PHAFA#X0,
			D	R5F100PJAFA#X0, R5F100PKAFA#X0, R5F100PLAFA#X0 R5F100PFDFA#V0, R5F100PGDFA#V0, R5F100PHDFA#V0, R5F100PJDFA#V0, R5F100PKDFA#V0, R5F100PLDFA#V0
			G	R5F100PFDFA#X0, R5F100PGDFA#X0, R5F100PHDFA#X0, R5F100PJDFA#X0, R5F100PKDFA#X0, R5F100PLDFA#X0 R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0,
			G	R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0, R5F100PFGFA#X0, R5F100PGGFA#X0, R5F100PHGFA#X0,
				R5F100PJGFA#X0
		Not	A	R5F101PFAFA#V0, R5F101PGAFA#V0, R5F101PHAFA#V0,
		mounted		R5F101PJAFA#V0, R5F101PKAFA#V0, R5F101PLAFA#V0 R5F101PFAFA#X0, R5F101PGAFA#X0, R5F101PHAFA#X0,
			D	R5F101PJAFA#X0, R5F101PKAFA#X0, R5F101PLAFA#X0 R5F101PFDFA#V0, R5F101PGDFA#V0, R5F101PHDFA#V0,
				R5F101PJDFA#V0, R5F101PKDFA#V0, R5F101PLDFA#V0 R5F101PFDFA#X0, R5F101PGDFA#X0, R5F101PHDFA#X0,
				R5F101PJDFA#X0, R5F101PKDFA#X0, R5F101PLDFA#X0

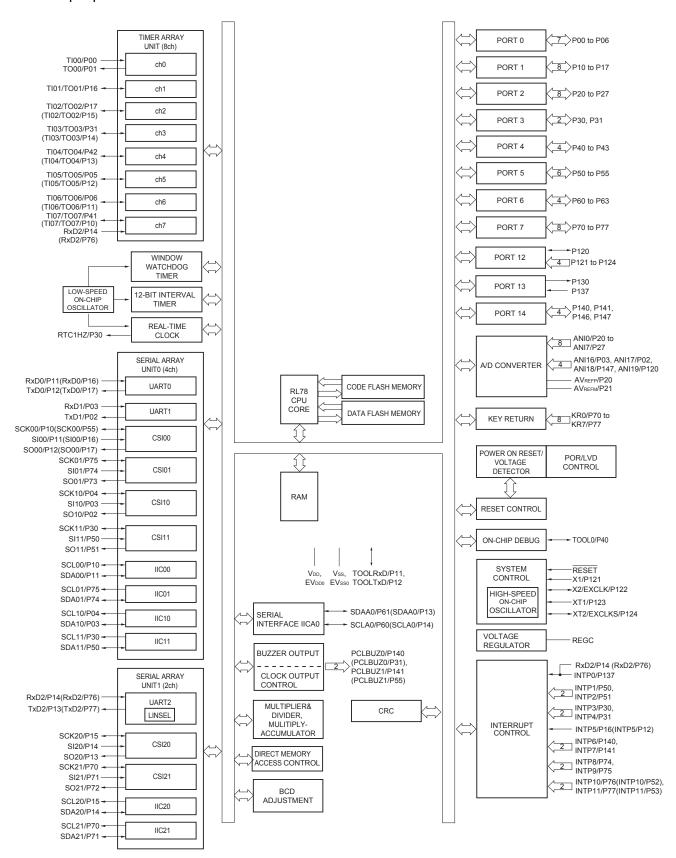
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



RL78/G13 1. OUTLINE

# 1.5.11 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

RL78/G13 1. OUTLINE

**3.** The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

4. When setting to PIOR = 1

11	<b>n</b>	n	١
14	ر2	_	ı

Ite	Item		20-pin 24-pin		25-pin		30-	-pin	32	-pin	36	pin	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzze	er output	- 1 1 2 2 2									2		
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation)											
8/10-bit resolution	A/D converter	6 channels 6 channels 6 channels 8 channels 8 channels 8 channels											
Serial interface		[20-pin,	24-pin,	25-pin p	roducts]								
		• CSI:	1 chann	el/simpli	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel				
		• CSI:	1 chann	el/simpli	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel				
		[30-pin,	32-pin <sub> </sub>	products	]								
		• CSI:	1 chann	el/simplit el/simplit el/simplit	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel	ng LIN-bi	us): 1 ch	annel	
		[36-pin	products	s]									
		• CSI:	1 chann	el/simplit el/simplit els/simpl	fied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanı	nel	rtina LIN	-bus): 1	channel	
	I <sup>2</sup> C bus			1 chanı		1 chanı		1 chan		1 chan		1 chan	nel
Multiplier and divid	der/multiply-	<ul> <li>16 bits × 16 bits = 32 bits (Unsigned or signed)</li> <li>32 bits ÷ 32 bits = 32 bits (Unsigned)</li> <li>16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)</li> </ul>											
DMA controller		2 channels											
Vectored interrupt	Internal	2	23	2	24	2	24	2	27	2	27	2	27
sources	External	;	3		5		5		6		6		6
Key interrupt		_											
Reset		<ul><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li></ul>	nal reset nal reset nal reset nal reset	SET pin by watc by power by volta by illega by illega by illega	er-on-res ge detec al instruc I parity e	set ctor tion exec rror		e					
Power-on-reset cir	cuit		er-on-res er-down-	set: 1	I.51 V (T I.50 V (T	,							
Voltage detector		Rising edge: 1.67 V to 4.06 V (14 stages)     Falling edge: 1.63 V to 3.98 V (14 stages)											
On-chip debug fun	ection	Provide	ed										
Power supply volta	age	V <sub>DD</sub> = 1	.6 to 5.5	V (T <sub>A</sub> =	-40 to +8	35°C)							
		$V_{DD} = 2$	4 to 5.5	V (T <sub>A</sub> = -	40 to +1	05°C)							
Operating ambient	t temperature			C (A: Co i°C (G: Ir				ndustria	l applica	tions )			
		14 - 40	.∪ <b>⊤</b> 100	. o (a. 11	idudilidi	αργιισατι	0110)						

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

# (3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high main)	•	LS (low main)	•	LV (low- main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fс∟к	$2.7~V \leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			$2.4~V \leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			$1.8~V \le EV_{DD0} \le 5.5$ V	500		500		1000		ns
			$1.7~V \le EV_{DD0} \le 5.5$ V	1000		1000		1000		ns
			$1.6~V \le EV_{DD0} \le 5.5$ V	_		1000		1000		ns
SCKp high-/low-level width	tkhi, tkli	4.0 V ≤ EV <sub>D</sub>	00 ≤ 5.5 V	tксү1/2 – 12		tксу1/2 — 50		tксү1/2 – 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tксү1/2 – 18		tксу1/2 — 50		tксү1/2 – 50		ns
				tксү1/2 – 38		tксу1/2 — 50		tксү1/2 — 50		ns
				tксү1/2 — 50		tксү1/2 — 50		tксү1/2 – 50		ns
				tксу1/2 — 100		tксу1/2 — 100		tксу1/2 — 100		ns
		1.6 V ≤ EVD	<sub>00</sub> ≤ 5.5 V	_		tксу1/2 — 100		tксу1/2 — 100		ns
SIp setup time	tsıĸı	4.0 V ≤ EV <sub>DI</sub>	00 ≤ 5.5 V	44		110		110		ns
(to SCKp↑)		2.7 V ≤ EV <sub>DI</sub>	00 ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EV <sub>DI</sub>	00 ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EV <sub>DI</sub>	oo ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EV <sub>DI</sub>	oo ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EV <sub>DI</sub>	00 ≤ 5.5 V	_		220		220		ns
SIp hold time	tksi1	1.7 V ≤ EV <sub>DI</sub>	00 ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EV <sub>DI</sub>	00 ≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$1.7 \text{ V} \le \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			25		25		25	ns
output Note 3		$1.6 \text{ V} \leq \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			_		25		25	ns

**Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

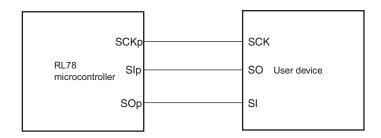
# (4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

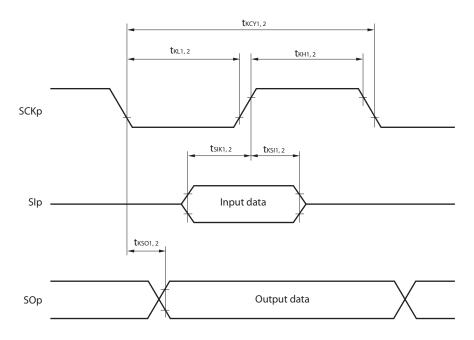
Parameter	Symbol	Condit	ions	, ,	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY2	$4.0~V \le EV_{DD0} \le 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмск ≤ 20 MHz	6/ƒмск		6/fмск		6/fмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмск ≤ 16 MHz	6/ƒмск		6/fмск		6/fмск		ns
		$2.4~V \le EV_{DD0} \le 5.5~V$		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
	$1.8 \text{ V} \le \text{EV}_{\text{DDO}} \le 5.5 \text{ V}$ $1.7 \text{ V} \le \text{EV}_{\text{DDO}} \le 5.5 \text{ V}$		$1.8~V \leq EV_{DD0} \leq 5.5~V$			6/fмск and 750		6/fмск and 750		ns
				6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5	V	_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tkH2, tkL2	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		tксү2/2 – 7		tксү2/2 - 7		tkcy2/2 -7		ns
		$2.7~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксу2/2 — 8		tксу2/2 - 8		tkcy2/2 -8		ns
		1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		tксү2/2 – 18		tксу2/2 - 18		tксу2/2 - 18		ns
		1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		tксү2/2 — 66		tксү2/2 - 66		tkcy2/2 - 66		ns
		1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5	V	_		tксү2/2 - 66		tkcy2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

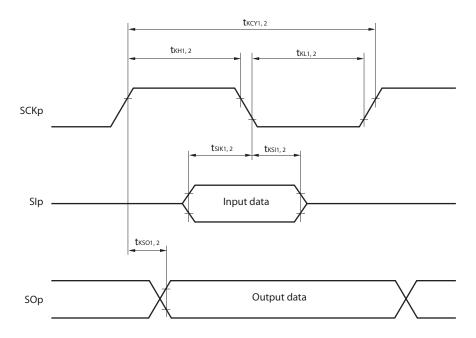
## CSI mode connection diagram (during communication at same potential)



# CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



# CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

# (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

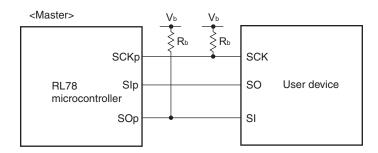
Parameter	Symbol	Conditions		HS (hig	h-speed Mode	`	r-speed Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\begin{split} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 & \ pF, \ R_b = 1.4 \ k\Omega \end{split}$	300		1150		1150		ns
			$\begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	500		1150		1150		ns
			$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{Note}, \end{aligned}$	1150		1150		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq$ $C_{b} = 30 \text{ pF},$	4.0 V,	tксү1/2 – 75		tксү1/2 – 75		tксу1/2 — 75		ns
		$2.7 \text{ V} \le \text{EV}_{DD}$ $2.3 \text{ V} \le \text{V}_{b} \le$ $C_{b} = 30 \text{ pF},$	00 < 4.0 V, 2.7 V,	tксу1/2 — 170		tксу1/2 — 170		tксу1/2 — 170		ns
		$1.8 \text{ V} \le \text{EV}_{DD}$ $1.6 \text{ V} \le \text{V}_{b} \le \text{C}_{b} = 30 \text{ pF},$	00 < 3.3 V, 2.0 V <sup>Note</sup> ,	tксү1/2 – 458		tксү1/2 – 458		tксү1/2 – 458		ns
SCKp low-level width	t <sub>KL1</sub>	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq$	00 ≤ 5.5 V, 4.0 V,	tксу1/2 — 12		tксү1/2 — 50		tксү1/2 — 50		ns
		$C_b = 30 \text{ pF},$ $2.7 \text{ V} \leq \text{EVor}$ $2.3 \text{ V} \leq \text{V}_b \leq$ $C_b = 30 \text{ pF},$	00 < 4.0 V, 2.7 V,	tксү1/2 — 18		tксү1/2 — 50		tксү1/2 — 50		ns
		$1.8 \text{ V} \leq \text{EV}_{DD}$ $1.6 \text{ V} \leq \text{V}_{b} \leq$ $C_{b} = 30 \text{ pF},$	00 < 3.3 V, 2.0 V <sup>Note</sup> ,	tксү1/2 — 50		tксү1/2 – 50		tксу1/2 — 50		ns

Note Use it with  $EV_{DD0} \ge V_b$ .

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

## CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R<sub>b</sub>[Ω]:Communication line (SCKp, SOp) pull-up resistance, C<sub>b</sub>[F]: Communication line (SCKp, SOp) load capacitance, V<sub>b</sub>[V]: Communication line voltage
  - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number , n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
  - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

**Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.

<R>

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 



#### (2) I2C fast mode

(Ta = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Сог	nditions	, ,	h-speed Mode	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7~V \leq EV_{DD0} \leq 5.5~V$	0	400	0	400	0	400	kHz
		fc∟κ≥ 3.5 MHz	1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
condition		1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		0.6		0.6		0.6		μS
Hold time <sup>Note 1</sup>	thd:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
Hold time when SCLA0 =	tLOW	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	1.3		1.3		1.3		μS
" <u>L</u> "		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1.3		1.3		1.3		μS
Hold time when SCLA0 =	<b>t</b> HIGH	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
"H"		1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		0.6		0.6		0.6		μS
Data setup time	tsu:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	100		100		100		μS
(reception)		1.8 V ≤ EV <sub>DD0</sub> ≤ 5.8	5 V	100		100		100		μS
Data hold time	thd:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0	0.9	0	0.9	0	0.9	μS
(transmission)Note 2		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0	0.9	0	0.9	0	0.9	μS
Setup time of stop	tsu:sto	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.$	5 V	0.6		0.6		0.6		μS
condition		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.8$	5 V	0.6		0.6		0.6		μS
Bus-free time	<b>t</b> BUF	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	1.3		1.3		1.3		μS
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	1.3		1.3		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode:  $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$ 

<R>

<R>

#### (3) I2C fast mode plus

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ 

Parameter	Symbol	Cor	nditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fcLk≥ 10 MHz	.		1000	_		_		kHz
Setup time of restart condition	tsu:sta	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			_	_	_	_	μS
Hold time <sup>Note 1</sup>	thd:STA	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$	5 V	0.26		_	-	_	_	μS
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			_		_		μS
Hold time when SCLA0 = "H"	tніgн	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	5 V	0.26		_		_		μS
Data setup time (reception)	tsu:dat	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	5 V	50		_	-	_	_	μS
Data hold time (transmission) <sup>Note 2</sup>	thd:dat	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	5 V	0	0.45	_	-	_	_	μS
Setup time of stop condition	tsu:sto	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	5 V	0.26			_	_	_	μs
Bus-free time	tbuf	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5	5 V	0.5		_	_	_	_	μS

**Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.

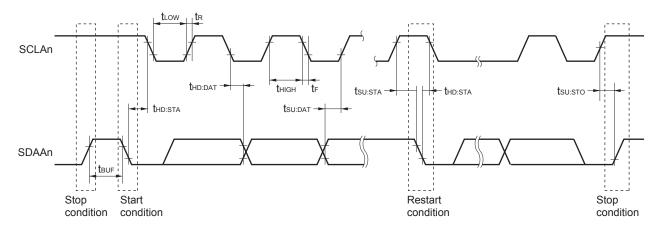
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus:  $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$ 

#### **IICA** serial transfer timing



**Remark** n = 0, 1

**Remark** The electrical characteristics of the products G: Industrial applications (T<sub>A</sub> = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **3.1** to **3.10**.

## 3.1 Absolute Maximum Ratings

## Absolute Maximum Ratings ( $T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V <sub>DD</sub>		-0.5 to +6.5	٧
	EV <sub>DD0</sub> , EV <sub>DD1</sub>	EV <sub>DD0</sub> = EV <sub>DD1</sub>	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V <sub>DD</sub> +0.3 <sup>Note 1</sup>	V
Input voltage	Vıı	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV <sub>DD0</sub> +0.3	V
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	and -0.3 to V <sub>DD</sub> +0.3 <sup>Note 2</sup>	
	V <sub>I2</sub>	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V <sub>DD</sub> +0.3 <sup>Note 2</sup>	V
Output voltage	V <sub>O1</sub>	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV <sub>DD0</sub> +0.3	٧
		P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	and -0.3 to V <sub>DD</sub> +0.3 <sup>Note 2</sup>	
	V <sub>02</sub>	P20 to P27, P150 to P156	-0.3 to V <sub>DD</sub> +0.3 Note 2	٧
Analog input voltage	VAI1	ANI16 to ANI26	$-0.3$ to EV <sub>DD0</sub> +0.3 and $-0.3$ to AV <sub>REF</sub> (+) +0.3 $^{\text{Notes 2, 3}}$	V
	V <sub>Al2</sub>	ANI0 to ANI14	$-0.3$ to V <sub>DD</sub> +0.3 and -0.3 to AV <sub>REF</sub> (+) +0.3 $^{\text{Notes 2, 3}}$	V

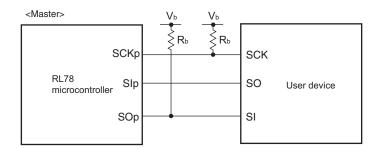
- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
  - 2. Must be 6.5 V or lower.
  - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
  - 2.  $AV_{REF}(+)$ : + side reference voltage of the A/D converter.
  - 3. Vss : Reference voltage



#### CSI mode connection diagram (during communication at different potential)



- Remarks 1.  $R_b[\Omega]$ :Communication line (SCKp, SOp) pull-up resistance,  $C_b[F]$ : Communication line (SCKp, SOp) load capacitance,  $V_b[V]$ : Communication line voltage
  - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
  - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

# 3.6 Analog Characteristics

## 3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = V <sub>BGR</sub>
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (–) = AVREFM
ANI0 to ANI14	Refer to <b>3.6.1 (1)</b> .	Refer to <b>3.6.1 (3)</b> .	Refer to <b>3.6.1 (4)</b> .
ANI16 to ANI26	Refer to <b>3.6.1 (2)</b> .		
Internal reference voltage	Refer to <b>3.6.1 (1)</b> .		-
Temperature sensor output			
voltage			

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	10-bit resolution AVREFP = VDD Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Full-scale error <sup>Notes 1, 2</sup>	Ers	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Integral linearity error	ILE	10-bit resolution AVREFP = VDD Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±1.5	LSB
Analog input voltage	Vain	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage out (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS (high			VBGR Note 4		V
		Temperature sensor output volume (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS (high	· ·		VTMPS25 Note	4	V

(Notes are listed on the next page.)



# 3.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.4~V \leq V \text{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites	Cerwr	Retained for 20 years  TA = 85°C Note 4	1,000			Times
Number of data flash rewrites		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C Note 4	100,000			
		Retained for 20 years  TA = 85°C Note 4	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
  - 2. When using flash memory programmer and Renesas Electronics self programming library.
  - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
  - 4. This temperature is the average value at which data are retained.

# 3.9 Dedicated Flash Memory Programmer Communication (UART)

#### $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

## 4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA

R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA

R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA

R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA

Previous Code

MASS (TYP.) [g]

R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

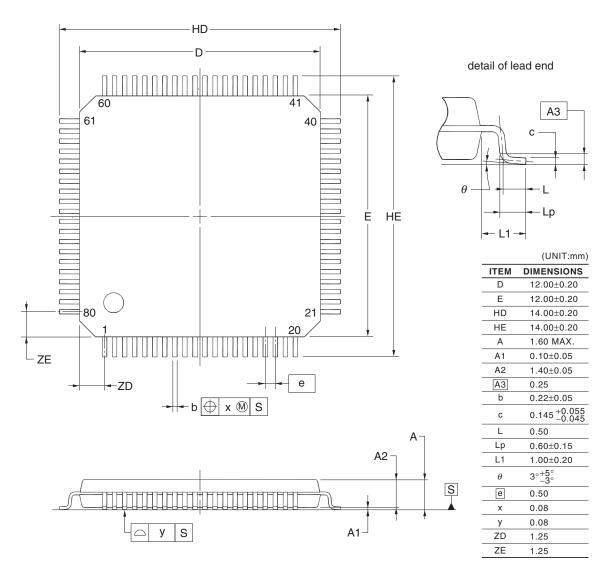
RENESAS Code

JEITA Package Code



R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB R5F100MFDFB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB R5F101MFDFB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB R5F100MFGFB, R5F100MGGFB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code Previous Code		MASS (TYP.) [g]	
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53	



#### NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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# RL78/G13 Data Sheet

			Description		
Rev.	Date	Page	Summary		
1.00	Feb 29, 2012	-	First Edition issued		
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count		
			corrected.		
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.		
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.		
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.		
		59, 63, 67	Descriptions of Note 8 in a table corrected.		
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.		
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.		
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.		
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.		
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.		
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.		
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.		
3.00	Aug 02, 2013	1	Modification of 1.1 Features		
		3	Modification of 1.2 List of Part Numbers		
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution		
		16 to 32	Modification of package type in 1.3.1 to 1.3.14		
		33	Modification of description in 1.4 Pin Identification		
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions		
		55	Modification of description in table of Absolute Maximum Ratings (T <sub>A</sub> = 25°C)		
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics		
		57	Modification of table in 2.2.2 On-chip oscillator characteristics		
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics		
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics		
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-		
		68	pin products  Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-		
		70	pin products  Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to		
		72	100-pin products  Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-		
			pin products		
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products		
		75	Modification of (4) Peripheral Functions (Common to all products)		
		77	Modification of table in 2.4 AC Characteristics		
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation		
		80	Modification of figures of AC Timing Test Points and External System Clock Timing		

		Description		
Rev.	Date	Page	Summary	
3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics	
		118	Modification of table and note in 2.6.3 POR circuit characteristics	
		119	Modification of table in 2.6.4 LVD circuit characteristics	
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode	
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics	
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes	
		123	Modification of caution 1 and description	
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T <sub>A</sub> = 25°C)	
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics	
		126	Modification of table in 3.2.2 On-chip oscillator characteristics	
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)	
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)	
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)	
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)	
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)	
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)	
		140	Modification of (3) Peripheral Functions (Common to all products)	
		142	Modification of table in 3.4 AC Characteristics	
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation	
		143	Modification of figure of AC Timing Test Points	
		143	Modification of figure of External System Clock Timing	
		145	Modification of figure of AC Timing Test Points	
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)	
		146	Modification of description in (2) During communication at same potential (CSI mode)	
		147	Modification of description in (3) During communication at same potential (CSI mode)	
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I <sup>2</sup> C mode)	
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)	
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)	
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)	
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)	
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)	
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)	

#### Notice

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California Eastern Laboratories, Inc.

4590 Patrick Henry Drive, Santa Clara, California 95054-1817, U.S.A Tel: +1-408-919-2500, Fax: +1-408-988-0279

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, German Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333 Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949 Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd. Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India Tel: +91-80-67208700, Fax: +91-80-67208777

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